PCN Number:		2	2014	1071	4001	1				PCN Dat	te:	07/16/2014	
Titl	le:	Qualificati	on of	FFA	B/M	IHO/	/RFAB	as a	additional Fab site	ор	tions for	sele	ect devices
Cus	stomer	Contact:	PCN	I Ma	nage	<u>er</u>	Phor		+1(214)480-603		Dept:	Qu	ality Services
*P	ropose	d 1 st Ship	Date:	•	10/	16/2	014		stimated Sample vailability:	1			te provided at nple request.
Cha	ange Ty	ype:											
	Assem	bly Site				Asse	embly	Pro	cess		Assem	bly	Materials
	Desigr	า				Elec	trical S	Spe	cification		Mecha	nica	l Specification
	Test S	ite							oing/Labeling		Test P	roce	SS
		Bump Site			Щ				Material				np Process
	Wafer	Fab Site							iterials		Wafer	Fab	Process
						Part			change				
							PCN	N D	etails				
De	scriptio	on of Chan	ge:										
		oups: (Aff MIHO8: A				es in	Prod	uct	Affected Sectio	n)			
		ess, Wafer						Δda	ditional Site Pro	CE	se Waf	ar D	ia
		BC7, 200m		CtCi				Additional Site, Process, Wafer Dia. FFAB, LBC7, 200mm					
	11100, L	<i>DC7</i> , 200111						, ,	ID, LDC7, 20011111				
		RFAB: Add											
		ess, Wafer		eter	•				ditional Site, Pro		ss, Wate	er D	ia.
L K	-AB, LBC	C7, 300mm	1					FFA	B, LBC7, 200mm				
Gı	roup 3	RFAB: Add	ding I	МІН	108								
Si	te, Proc	ess, Wafer	diame	eter				Ado	ditional Site, Pro	ces	ss, Wafe	er D	ia.
RF	AB, LB	C7, 300mm)					MIH	108, LBC7, 200m	m			
Gı	roup 4	MIHO6: A	dding	, MI	[HO	8							
Si	te, Proc	ess, Wafer	diam	eter			4	Additional Site, Process, Wafer Dia.					
M]	[H, 50A	12, 150mm)					MIHO8, 50A12, 200mm					
Gı	Group 5 MIHO8: Adding RFAB												
Site, Process, Wafer diameter				Additional Site, Process, Wafer Dia.					ia.				
					AB, LBC7, 300mm		•						
Qua	The LBC7 process was previously qualified at FFAB on 10/31/2007 and at MIHO on 1/14/2005. Qualification details are shown in the Qual Data Section of this document.												
		of Supply											
		of Supply	on Ec) rm	E:+	E	nction		uality or Reliabi	lite	(nociti	VC -	/ pogative):
		a ilipact	JII FC	JI 111	, rit	, ru	iiction	, Q	uanty of Kenabi	iity	(positi	ve /	negative):
INOI	None												

Changes to product identification resulting from this PCN:

Chip Site:

Current

Chip Site	Chip site code (20L)	Chip country code (21L)
RFAB	RFB	USA
MIHO6	MIH	JPN
MIHO8	MH8	JPN

New

Chip Site	Chip site code (20L)	Chip country code (21L)
FR-BIP-1	TID	DEU
MIHO8	MH8	JPN
RFAB	RFB	USA

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS MADE IN: Malays

MADE IN: Malaysia 2DC: 2Q: MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04

PTT: 39 LBL: 5A (L)TO:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$12

(P) (2P) REV: (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) AGO: MYS

Product Affected:

Group 1 MIHO8: Adding FFAB (LBC7)							
FX026	HPA02240RVER	TPS51363RVER	TPS51367RVET				
FX033	TPS51362RVER	TPS51363RVET	TPS59367RVER				
FX033Z	TPS51362RVET	TPS51367RVER	TPS59367RVET				
Group 2 RFAB: Addi	ng FFAB (LBC7)						
TPS65132A0YFFR	TPS65132B0YFFR	TPS65132B5YFFR	TPS65132LYFFR				
TPS65132AYFFR	TPS65132B2YFFR	TPS65132BYFFR	TPS65132YFFR				
Group 3 RFAB: Addin	ng MIHO8 (LBC7)						
BQ24295RGER	SN2807RGER	TPS54427DRCR	TPS54626PWP				
BQ24295RGET	SN2807RGET	TPS54427DRCT	TPS54626PWPR				
BQ24296RGER	SN2808RGER	TPS54428DDA	TPS54627DDA				
BQ24296RGET	SN2808RGET	TPS54428DDAR	TPS54627DDAR				
BQ24297RGER	SN2910RGER	TPS54428DRCR	TPS54628DDA				
BQ24297RGET	SN2910RGET	TPS54428DRCT	TPS54628DDAR				
SN2800RGER	TPS54427DDA	TPS54625PWP	TPS56628DDA				
SN2800RGET	TPS54427DDAR	TPS54625PWPR	TPS56628DDAR				
Group 4 MIHO6: Add	Group 4 MIHO6: Adding MIHO8 (50A12)						
TPA6013A4PWP	TPA6013A4PWPR						
Group 5 MIHO8: Add	ling RFAB (LBC7)						
TPS22993PRLWR	TPS22993PRLWT						

Reference Qualification Data: LBC7 Process at FFAB

Reference Qualification Data. EDG/ 1100033 dt 11745								
Qualification Data: (Approved: 10/31/2007)								
This qualification has been developed	This qualification has been developed for the validation of this change. The qualification data wi							
validate that the proposed change me	ets the applicable re	leased technica	al specific	ations.				
Qualific	Qualification Device: TCA6416PW							
Wafer Fab Site: FFAB	Metallization:	TiN/AlCu.5/Ti	N					
Wafer Fab Process: LBC7	Wafer diameter:	200mm						
Qualification: Plan Test	Results							
Reliability Test	Conditions		Sample Size /Fail		/Fail			
Reliability Test	Conditions		Lot#1	Lot#2	Lot#3			
** Steady-State Life Test 150C	300 Hrs		116/0	116/0	116/0			
**Biased HAST, 130C/85%RH	96 hours		77/0	77/0	77/0			
**Autoclave 121C	96 Hrs		77/0	77/0	77/0			
**Temp Cycle -65C/+150C	1000 Cycles		77/0	77/0	77/0			
**High Temp. Storage Bake 150C	1000 Hours		77/0	77/0	77/0			
ESD HBM	1000V		3/0	-	-			
ESD CDM	250V		3/0	-	-			
Latch-up	(per JESD78, Class II)		9/0	-	-			
Electrical Char	Per datasheet spec		Pass	Pass	Pass			
Manufacturability	(approved by mfg. site)		Pass	Pass	Pass			
**Preconditioning: MSL 1@260C	, , , , , , , , , , , , , , , , , , , ,							

Reference Qualification Data: LBC7 Process at MIHO8

Reference Qualification Data: LBC/ Process at MIHO8							
Qualification Data: (Approved 01/14/2005)							
This qualification has been developed for the validation of this change. The qualification data will							
validate that the proposed cha	validate that the proposed change meets the applicable released technical specifications.						
	Qual Vehicle: 1	TPS62110RSA					
Wafer Fab Site: M	IHO8	Metall	ization:	TiN/AlCu.5/	TiN		
Wafer Fab Process: LE	3C7	Die Protective C	Coating:	Oxynitride 8	3000A		
Qualification: Plan	☐ Test Results						
Reliability Test	Conditions		S	Sample Size /	e Size /Fail		
Reliability Test	Conditions		Lot#1	Lot#2	Lot#3		
**Life Test, 140C	480 Hours		130/0	130/0	130/0		
**HAST 130C/85%RH	96 Hours	77/0	77/0	77/0			
**Autoclave, 121C	240 Hours	240 Hours			77/0		
**Thermal Shock, -65/150C	1000 Cycles	1000 Cycles		77/0	77/0		
**Temp Cycle, -65/+150C	1000 Cycles		77/0	77/0	77/0		
**High-Temp Storage, 170C	420 hours		77/0	77/0	77/0		
ESD HBM	1000V		3/0	3/0	3/0		
ESD CDM	250V		3/0	3/0	3/0		
Latch-up @ 70C	(per JESD78)	(per JESD78)		5/0	5/0		
Electrical Characterization	Per datasheet sp	Per datasheet spec		PASS	PASS		
Manufacturability	Wafer Fab Appro	Wafer Fab Approved		PASS	PASS		
Manufacturability	Assembly Site Ap	oproved	PASS	PASS	PASS		
**Preconditioning: MSL 2@260C							

Reference Qualification Data: 50A12 Process at MIHO8 Qualification Data: (1/08/2010)

This qualification has been developed for the validation of this change. The qualification data validates that the proposed change meets the applicable released technical specifications.							
	Qual Vehicle 1: TLV5630IDW						
Wafer Fab Site:	Wafer Fab Site: MIHO 8 (MIHO) Wafe						
Wafer Fab Process:	50A12		·				
Qualification: Plan Test Results							
Reliability Test	Conditions	Sample Size (PASS/F			SS/FAIL)		
Reliability Test	Conditions		Lot#1	Lot#2	Lot#3		
Life Test	125C, 1000 Hrs		112/0	112/0	112/0		
Biased Temp Humidity	85C/85%RH(500 H	Hrs)	77/0	77/0	77/0		
Autoclave*	+121C, 240 Hrs.		77/0	77/0	77/0		
Temp Cycle*	-65/+150C, 1000	cycles	77/0	77/0	77/0		
Thermal Shock*	-65/150C, 1000 Cy	ycles	77/0	77/0	77/0		
High Temp Storage Bake	+150C, 1000 Hrs.		77/0	77/0	77/0		
ESD - HBM (3 Units/level)	500V, 1kV, 1.5kV,	500V, 1kV, 1.5kV, 2kV			12/0		
ESD - CDM (3 Units/level)	500V	3/0	3/0	3/0			
*Preconditioning: Level 2 @	@ 260C						
Qual Vehicle 2: TPA6203A1DRB							
Wafer Fab Site: MIHO 8 (MIHO) Wafe				r Size 200 mm			
Wafer Fab Process:	50A12						
Qualification: Plan	☐ Test Results						
Deliebility Teet	Canditiana	Sample Size (PASS			S/FAIL)		
Reliability Test	Conditions	·	Lot#1	Lot#3			
Manufacturability (Wafer Fab)	Per mfg. site spec		Pass	-	-		
Electrical Characterization	Side by side comparison		30/0	-	-		
	Qual Vehicle 3: TPA6205A1DRB						
Wafer Fab Site:	MIHO 8 (MIHO)	Wafer	Size 200	mm			
Qualification: Plan	50A12 ∑ Test Results						
	☐ Test Results		Sample	Size (PAS	S/FAIL)		
			Sample Lot#1	Size (PAS	S/FAIL) Lot#3		
Reliability Test	☐ Test Results		•				

Reference Qualification Data: LBC7 Process at RFAB Qualification Data - (Approved 06/03/2014)

Attributes	Qual Device: TPS22993PRLW	QBS Process: TPS54620RGYR	QBS Process: CD3230A0YFF
Wafer Fab Site	RFAB	RFAB	RFAB
Wafer Fab Process	LBC7	LBC7	LBC7
Wafer Diameter	200mm	200mm	200mm

Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as: Number of lots / Total sample size / Total famed						
Туре	Test Name / Condition	Duration	QBS Product: TPS22993PRLW	QBS Process: TPS54620RGYR	QBS Process: CD3230A0YFF		
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0	_	3/250/0		
				0/000/0	3/230/0		
AC	Autoclave 121C	96 Hours	3/267/0	6/230/0	<u>-</u>		
UHAST	Unbiased HAST 130C/85%RH	96 Hours	-	-	2/169/0		
TC	Temperature Cycle, -55/125C	700 cycles	-	-	2/164/0		
TC	Temperature Cycle, -65/150C	500 Cycles	3/269/0	6/231/0	-		
HTSL	High Temp Storage Bake 150C	1000 Hours	3/273/0	-	-		
HTSL	High Temp Storage Bake 170C	420 Hours		6/231/0	3/239/0		
HTOL	Life Test, 125C	1000 Hours	-	-	3/240/0		
HTOL	Life Test, 150C	300 Hours	1/79/0	-	-		
HTOL	Life Test, 155C	240 Hours	-	6/228/0	-		
НВМ	ESD - HBM	1000 V	1/3/2000	3/9/2000	3/9/2000		
CDM	ESD - CDM	250 V	1/3/2000	3/9/2000	3/9/2000		
LU	Latch-up	(per JESD78)	1/6/2000	6/18/2000	3/36/0		
ED	Electrical Characterization.	Per Datasheet Parameters	1/Pass	-	3/Pass		

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com